

ABSTRACT OF THE DISCLOSURE

A memory cell of a semiconductor device and a method for forming the same, wherein the memory cell includes a substrate having active regions and field regions, a gate layer formed over the substrate, the gate layer including a plurality of access gates formed over the active regions of the substrate and a plurality of pass gates formed over the field regions of the substrate, first self-aligned contact regions formed between adjacent pass gates and access gates, and second self-aligned contact regions formed between adjacent access gates, wherein a width of each of the first self-aligned contact regions is larger than a width of each of the second self-aligned contact regions.